

Control strategies for solution-processed ZTO-based thin-film transistors tailored toward volatile organic compound detection

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Abstract

We present a breakthrough in the fabrication of amorphous Zn-Sn-O (ZTO)-based thin film transistors (TFTs) for volatile organic compound (VOC) detection. The incorporation of highly abundant materials offers substantial economic and environmental benefits. However, analyses

for the design of a multilayer channel are still limited. This work demonstrates that the chemical environment influences ZTO-based TFTs' carrier transport properties and can be tailored for detecting specific VOCs, ensuring high specificity in diagnosing life-threatening conditions through simple breath analysis. We adopt a low-cost, high-throughput, fully solution-processed ZTO and ZnO multilayering strategy. Our in-depth compositional and morphological analyses reveal that low surface roughness, excellent Zn and Sn intermixing, high oxygen vacancy (31.2 %), and M-OH bonding (11.4 %) contents may account for the outstanding electrical and sensing performance of ZTO-ZTO TFTs. Notably, these TFTs achieve near-zero threshold voltage (2.20 V), excellent switching properties (10^7), and high mobility ($10 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$). This results in high responsivity to alcohol vapors at low-voltage operation with peak responsivity for methanol ($R = 1.08 \times 10^6$) over two orders of magnitude greater than acetone. When miniaturized, these devices serve as easy-to-operate sensors, capable of detecting VOCs with high specificity in ambient conditions.

1. Introduction

Abnormal concentrations of VOCs in human breath serve as disease-specific biomarkers for real-time, non-invasive diagnosis of medical conditions. One such example is methanol poisoning outbreaks after the consumption of adulterated alcohol, which frequently overwhelm health care facilities in developing countries with devastating consequences including organ failure, blindness, and even death.^[1–3] Rapid detection for the screening of laced beverages is vital and can be enabled by measuring methanol concentration in human breath. This concentration is approximately 0.4 ppm for a healthy individual. However, laboratory-based screening tools such as gas chromatography-mass spectrometry typically require long processing times, trained professionals, and expensive instrumentation.^[4,5] Therefore, the development of point-of-care sensors that are simple to operate and can distinguish methanol from other VOCs in ambient conditions has important societal benefits.^[6]

Chemiresistive gas sensors that incorporate highly abundant materials such as zinc oxide (ZnO), tin oxide (SnO_2) and Zn-Sn-O (ZTO) have been widely publicised thanks to their high mobility, environmental stability, and ease of fabrication.^[7–15] Their working principle is straightforward and reversible, based on changes in the electrical resistance of the metal oxide when exposed to different concentrations of the target gases. Solution-processed thin-film transistors (TFTs) have shown great promise for next-generation high throughput chemiresistive gas sensing for inexpensive point-of-care testing applications. The gate electrode modulates the conductivity

of the TFT, and changes in drain-source current (I_{ds}) are measured between source-drain electrodes to yield an amplified response.^[16–18] Recently, we have demonstrated the facile detection of acetone vapors for the early symptom detection of diabetes using SnO_2 TFTs under ambient conditions. I_{ds} increased following exposure as acetone underwent a redox reaction with the adsorbed oxygen species on the semiconductor surface, which resulted in free electrons being released back into the conduction band.^[19]

Sensor responsivity (R) at low-voltage operation is dictated by two key parameters, current on/off ratio ($I_{on/off} \geq 10^7$) and threshold voltage (V_{th}), which should be near-zero to realise mobile applications with low power requirements. Zan *et al.* showed that low V_{th} (< 5 V) and high $I_{on/off}$ ($> 10^6$) exhibited by amorphous In-Ga-Zn-O (a-IGZO) TFTs capped with an organic sensing layer led to high sensitivity to acetone vapor with a limit of detection of 100 ppb (see **Table S9**).^[20] Various approaches have been reported to improve the chemiresistive properties of metal oxide TFTs, including defect engineering and Sn doping, by which their electronic structure and surface morphology can be precisely tuned. The introduction of oxygen vacancies promotes the chemisorption of oxygen molecules onto the metal oxide surface, enabling enhanced sensitivity and shortened response time for VOC detection.^[21] The latter involves the introduction of Sn, which can create smooth amorphous films and offers advantages with regards to large-scale uniformity and the possibility of miniaturization.^[22,23] The origin of the electrical and chemiresistive properties of single-layer TFTs is well understood.^[18] However, detailed morphological and structural analyses of stacked and alternating layers are limited to date. The design of a multilayer channel has been shown to enhance reliability and charge transport.^[24–26]

In this work, we demonstrate a strategy for enhanced functional performance via the multilayering of solution-processed metal oxide semiconductors. We used ZnCl_2 and SnCl_2 precursors to successfully fabricate bottom gate top contact TFTs grown by the sequential deposition and thermal treatment of ZTO and ZnO. The electrical properties of the ZTO-based TFTs were heavily influenced by several factors, including film composition, layering and surface morphology. The judicious control of film thickness was facilitated by rigorous structural and compositional analyses of the multilayer metal oxide films. Secondly, we qualitatively assessed the interrelation between oxygen vacancy content and gas sensing performance to demonstrate VOC detection proof-of-concept. The resulting low power consumption and high signal-to-noise ratio of the measured functionality exceeds the existing

literature and will facilitate a detailed quantitative sensing study that will be reported in the future.^[27–31]

2. Results and Discussion

2.1. Optimization of the Charge Transport Layer

We adopted a simple design strategy to tailor the electrical and sensing performance of metal oxide TFTs, which involved the layering of spin-coated ZTO and ZnO thin films. ZnO was studied as it is well-known that ZnO nanostructures grown on the surface of ZTO enhance electron injection in other solution-processed devices.^[32] To highlight the benefit of controlling film thickness and morphology via the sequential spin-casting and thermal treatment of metal oxide layers, our preliminary study compared the electronic performance of a single layer ZTO TFT prepared from a precursor solution with double the concentration against the ZTO-ZTO TFT presented in **Figure 1(a)**. Next, we assessed the thermal treatment of ZTO-ZTO bilayer films by annealing the layers at increasing temperatures. **Figure 1(a)** shows a schematic of the device and **Figure 1(b)**, the TGA. A detailed description is given in supporting information (**Figure S1 & Table S2**). We then compared the electrical performance of monolayer and bilayer ZTO-based TFTs treated at the optimum temperature of 500 °C. The spin-coating parameters were maintained at 5000 rpm for 30 s to control the film thickness and ensure long-range homogeneity. Effective mobility (μ_{eff}) and V_{th} of the ZTO-ZTO TFTs were extracted using **Equations (1)-(4)** from the I_{ds} against applied gate bias, V_{gs} , transfer characteristics presented in **Figure 1(c)**.

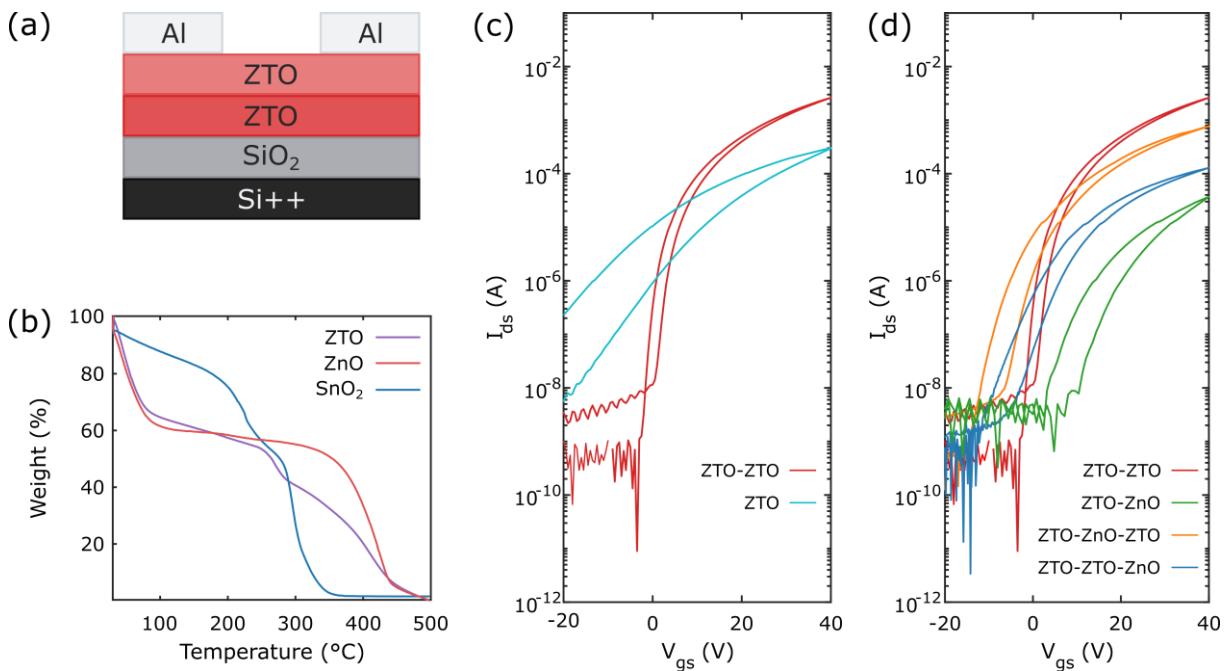


Figure 1. (a) Schematic of ZTO-ZTO TFT. (b) TGA curves for ZTO, ZnO and SnO₂ solutions. (c) Transfer characteristics in the saturation regime at $V_{ds} = 40$ V and $V_{gs} = -20$ to 40 V for the ZTO and ZTO-ZTO TFTs treated at 500 °C. (d) Transfer characteristics in the saturation regime at $V_{ds} = 40$ V and $V_{gs} = -20$ to 40 V for the bilayer and trilayer TFTs treated at 500 °C.

Electronically, the ZTO TFT performed poorly in comparison to the ZTO-ZTO TFT, owing to pronounced hysteresis in the I_{ds} - V_{gs} measurements, that leads to a large V_{th} shift from -7.44 V to 3.84 V for the forward and backward sweeps of V_{gs} , respectively. Conversely, the ZTO-ZTO TFT exhibited excellent stability and minimal V_{th} shift, calculated as 2.20 V and 2.31 V for the forward and backward sweeps, respectively. Based on this successful result, a multilayering approach, involving the intercalation of a ZnO layer to construct bilayer and trilayer TFTs was explored. The resulting multilayers were all thermally treated at 500 °C following the previously discussed results, and their transfer characteristics are presented in **Figure 1(d)**.^[33] The ZTO-ZnO TFT exhibited large hysteresis, poor carrier mobility ($\mu_{eff} = 0.135$ cm²V⁻¹s⁻¹) and $I_{on/off} < 10^4$ than the former ZTO-ZTO TFT. In addition, the electrical properties of the ZTO-ZTO-ZnO TFT were inferior to those calculated for the ZTO-ZnO-ZTO TFT, which suggests that the deposition of the final ZnO layer impeded the efficiency of charge transport between the source-drain electrodes. Importantly, the low off-current and near-zero V_{th} of the ZTO-ZTO and ZTO-ZnO-ZTO TFTs allude that a high responsivity could be achieved at low-voltage operation in the presence of VOCs. The electronic parameters are summarized in **Table 1**.

Table 1. Electrical parameters obtained from monolayer and multilayer metal oxide TFTs treated at 500 °C.

Device	$I_{on/off}$	V_{th} [V]	μ [cm ² V ⁻¹ s ⁻¹]	μ_{eff} [cm ² V ⁻¹ s ⁻¹]
ZTO	10 ⁶	-7.44	0.775	0.741
ZTO ZnO	10 ⁴	5.36	0.148	0.135
ZTO ZTO	10 ⁷	2.20	10.2	9.49
ZTO ZnO ZTO	10 ⁶	-1.74	2.55	2.32

ZTO				
ZTO	10^5	-0.910	0.458	0.417
ZnO				

2.2. Growth and Structural Characterization of Metal Oxide Layers

To understand the physical basis of the enhanced electronic functionality, a detailed structural investigation was undertaken. The effect of inserting a ZnO layer on the crystalline properties of the ZTO-based films was investigated using X-ray reflectometry (XRR) and X-ray diffraction (XRD). The XRR results examined the interface width, film thickness and density of the metal oxide systems.^[26] **Figure 2(a)** shows that the period of these Kiessig fringes and fall in intensity were related to differences in film thickness and total interface width of the layers, respectively.^[26,34] The lower number of oscillating fringes for the monolayer compared to the bilayer and trilayer systems, are well represented by the best fitting simulations (solid black lines, **Table S3**), indicating that the monolayer is a thinner film. The position of the critical angle also shifted toward higher angles, which points towards denser films after the second and third layers were spin-coated and thermally treated. The curve shape around the critical angle was broader for the multilayer stacks, which suggests that the film density was not constant throughout the bulk of the bilayer and trilayer films.

The best fitting simulations of the XRR results were used to determine the scattering length density (SLD) plotted in **Figure 2(b)**, which show that the effective density increased from approximately $0.8 \text{ re}\text{\AA}^{-3}$ to $1.3 \text{ re}\text{\AA}^{-3}$ for the monolayer and bilayer films at the substrate ($Z \approx 0 \text{ nm}$), respectively. Film density remained constant before reaching the ZTO and ZTO-ZnO film surfaces, however, a clear drop was observed in the bulk of the ZTO-ZTO film at $Z \approx 7 \text{ nm}$. The same behaviour was observed for the trilayer systems as the film depth approached 10 nm, in agreement with the broadening around the critical angle. We infer that our spin-coated films were not organized in a traditional layer-by-layer heterostructure system with a single uniform interface. Instead, the first layer was compacted by the addition and thermal treatment of the second and third layers, giving rise to two distinct regions with different film densities.

Specular XRR cannot distinguish between topographical roughness and chemical intermixing of the interference between layers. Therefore, the variation in total interface width with sample depth shown by the shaded areas of **Figure 2(b)** considered both of these interface broadening mechanisms. The thickness of the ZTO film was estimated to be roughly 8 nm, which increased

to **over 15 nm** for the ZTO-ZTO film. Furthermore, the surface of these two films may have been smooth as the Kiessig fringes were observed at higher angles ($2\theta > 3.5^\circ$). Conversely, the thickness of the ZTO-ZnO film was notably more than that of the ZTO-ZTO film (> 20 nm), which, coupled with the Kiessig fringes only being present at lower angles ($2\theta < 2.5^\circ$), suggested a much rougher surface morphology than the other films. The maximum densities of the trilayer films were consistent with the movement of the critical angle toward $2\theta \approx 1^\circ$ and were between 1.4 g cm^{-3} and 1.6 g cm^{-3} , correlating with the addition of the third layer and compaction of the initial deposition.

XRD indicated that the ZTO-capped films (ZTO-ZTO and ZTO-ZnO-ZTO) were amorphous as they did not exhibit sharp diffraction peaks assignable to a crystalline phase (**Figure 2(c)**). These results are comparable with those of solution-processed films prepared using metal chlorides dissolved in 2-methoxyethanol at similar conditions reported in the literature.^[30,35–38] Nonetheless, the ZnO-capped films (ZTO-ZnO and ZTO-ZTO-ZnO) showed a small halo at $2\theta \approx 34.4^\circ$, ascribed to the hexagonal wurtzite structure of ZnO (002).^[39] The origin of this peak could be explained by the growth of Zn single crystal nanoparticles, which caused the increase in surface roughness and film thickness.

Finally, X-ray photoelectron spectroscopy (XPS) depth profiling was conducted to track the evolution of the Zn $2p_{3/2}$ and Sn $3d$ peak intensities and assess the possible gradients or migration of either component in our TFTs. Etch cycle zero corresponded to the film surface, and the etching was considered complete when the main signals present were the Si $2s$, Si $2p$ and O $1s$ peaks of the substrate, from etch cycle ten to twenty depending on the thickness of the film (**Figures S5-S6**). **Figure 2(d)** shows clear differences in Zn and Sn composition following the introduction of a ZnO layer. The ZTO-capped samples comprised films homogeneous in thickness and Zn/Sn distribution on the surface of the substrate, as the Zn $2p_{3/2}$ and Sn $3d$ signals diminished following the eighth etch cycle. It was noted that the Zn $2p_{3/2}$ and Sn $3d$ signals reached a plateau at maximum intensity around etch cycle five, which concurred with the two distinct regions of film density observed from XRR analysis. Conversely, the Zn $2p_{3/2}$ signal was still prominent beyond etch cycle twenty-five for the ZnO-capped samples. Furthermore, the signature of the Sn $3d$ signal rose sharply before reaching maximum intensity and was markedly reduced with respect to the Zn $2p_{3/2}$ signal for the ZTO-ZnO sample. The latter correlates well with the XRD results, which suggested Zn crystal growth in addition to the target material. The ZTO-ZnO film density also remained constant throughout the bulk of the film,

indicative of a single layer film that was predominantly Zn. Finally, the low metallic content recorded for the ZTO-ZnO film may have explained the poor electronic performance of the ZTO-ZnO TFT.

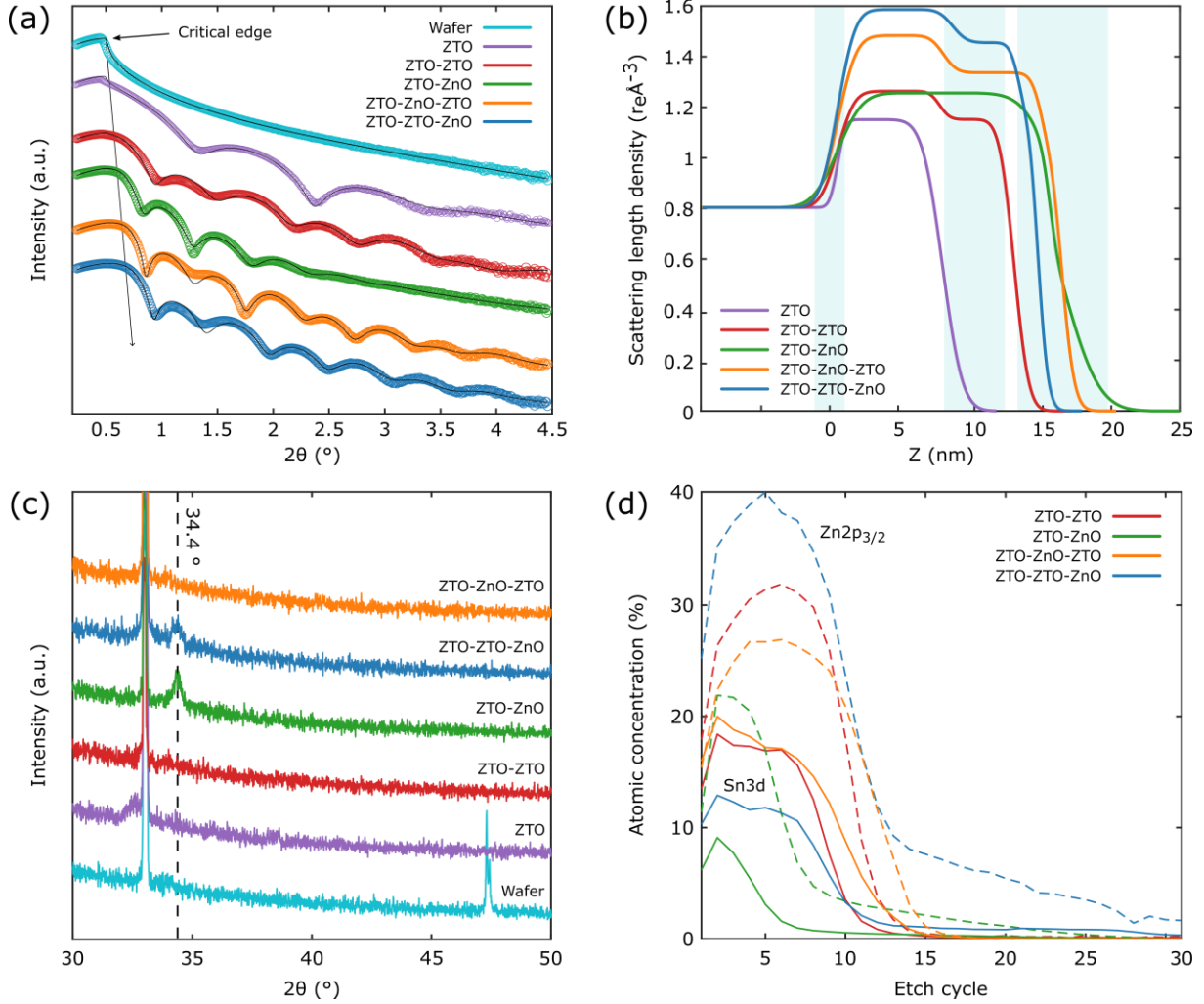


Figure 2. (a) Measured (symbols) and calculated (solid black lines) XRR spectra obtained from single, bilayer and trilayer metal oxide systems. (b) Extracted SLD versus depth profile (Z) for $2\theta = 0$ to 4.5° . (c) XRD measurements for $2\theta = 30$ to 50° . (d) XPS depth profile of $\text{Zn } 2p_{3/2}$ and $\text{Sn } 3d$.

To further investigate the clear differences in surface morphology and composition between the ZnO- and ZTO-capped films, TEM, SEM and AFM analyses were carried out on ZTO-ZnO-ZTO (**Figure 3(a)-(d)**) and ZTO-ZTO-ZnO films (**Figure 3(e)-(h)**), respectively.

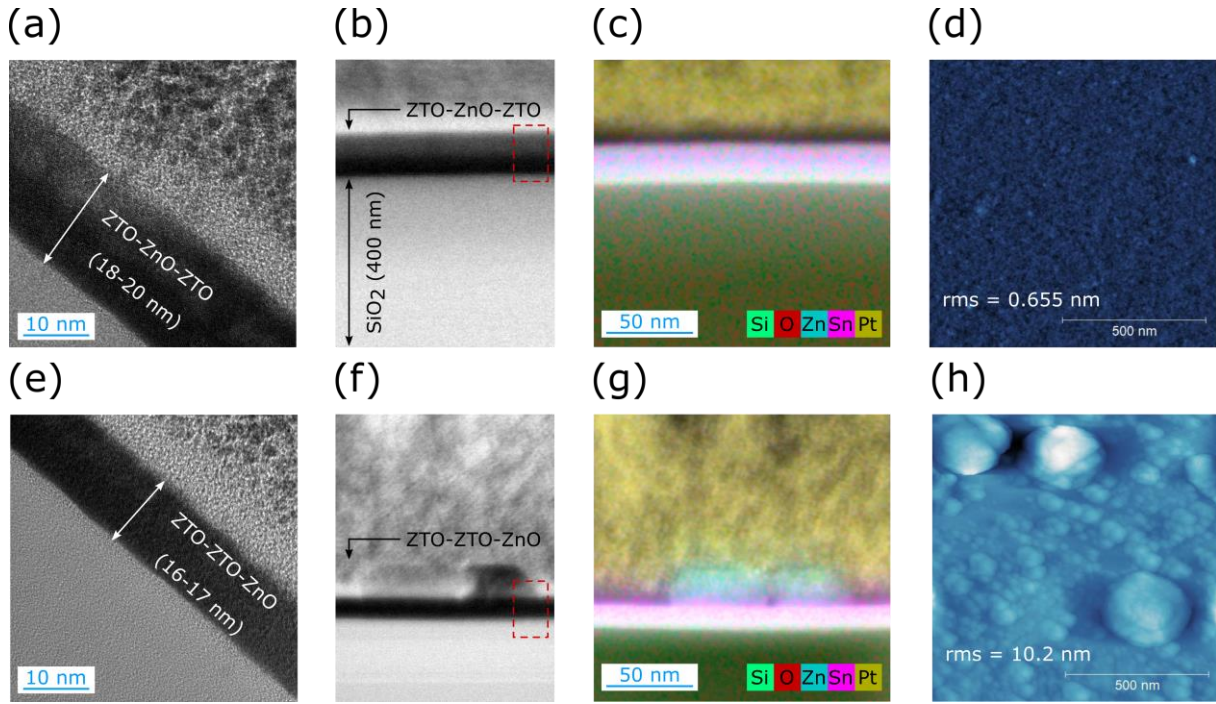


Figure 3. Morphological analysis of the (a)-(d) ZTO-ZnO-ZTO and (e)-(h) ZTO-ZTO-ZnO films. (a), (e) High- and (b), (f) low-magnification TEM images (red dashed square). (c), (g) Elemental mapping. (d), (h) AFM images ($1 \mu\text{m}^2$ scan area) with calculated rms surface roughness.

The high-magnification TEM image (**Figure 3(a)**) of the ZTO-ZnO-ZTO sample shows a homogenous film that has a thickness between 18 nm and 20 nm over a large region of the TFT (**Figure 3(b)**), in good agreement with XRR analysis. Complementary elemental mapping (**Figures 3(c) & S2(a)-(e)**) support the evolution of the Zn $2p_{3/2}$ and Sn 3d signals as the components were well mixed throughout the entire film. The AFM and SEM images (**Figures 3(d), S3(a)-(b) & S4(a), (c)-(d)**) of the ZTO-capped samples show amorphous films with surface roughness comparable to that of the substrate (0.655 nm),^[32] consistent with XRD analysis, while, the TEM images (**Figures 3(e)-(f)**) of the ZTO-ZTO-ZnO film confirmed the growth of crystalline features up to a micron in height, composed primarily of Zn observed from the elemental mapping of **Figures 3(g) & S2(f)-(j)**. As mentioned, these Zn single crystals brought about the small halo observed during XRD analysis at $2\theta \approx 34.4^\circ$ that corresponded to the hexagonal wurtzite structure of ZnO (002).^[32] The AFM and SEM images (**Figures 3(h), S3(c) & S4(b)**) of the ZnO-capped samples display increased surface roughness (10.2 nm) as a result of the small particles grown on the surface. These were accompanied by micron-sized crystalline features observed in the high-magnification TEM and were dispersed randomly on the surface of the substrate with a large distribution of particle sizes. The final ZTO layer may

have helped to planarize the film surface, which facilitated the cleaner deposition of source-drain electrodes and the establishment of charge percolation pathways that may be responsible for the enhanced electrical performance of the ZTO-capped TFTs.

Considering now the electronic environment, **Figures 4(a)-(b)** show the XPS spectra for the Zn 2p_{3/2} and Sn 3d components, which were calibrated against the C 1s peak centered at 284.6 eV to adjust for any charge induced shift during testing. The shift of Zn 2p_{3/2} peak to lower binding energy points towards increased oxygen vacancy content.^[40] The binding energies at 486.5 eV and 495 eV are separated by 8.5 eV and ascribed to Sn 3d_{5/2} and Sn 3d_{3/2} core levels, indicating the Sn⁴⁺ oxidation state.^[22] Therefore, Sn²⁺ of SnCl₂ in the precursor turned into Sn⁴⁺ in our ZTO films after thermal treatment at 500 °C in the air, which is the main component for n-type conduction.^[41,42] The presence of Sn has been known to enhance carrier density and suppress electron scattering effects due to the ionic radii of Zn²⁺ (0.074 nm) and Sn⁴⁺ (0.069 nm).^[22,23] The ZTO-capped films comprised the highest Sn content, calculated as 16.9 % and 17.2 %, respectively, for the bilayer and trilayer TFTs (**Table S5**). In contrast, the ZTO-ZnO film contained the lowest Sn content (3.1 %), attributed to the introduction of the ZnO final layer, which resulted in the formation of the aforementioned rough, particulate film. It is inferred that the low Sn content was responsible for the exceptionally low mobility calculated for the ZTO-ZnO TFT.

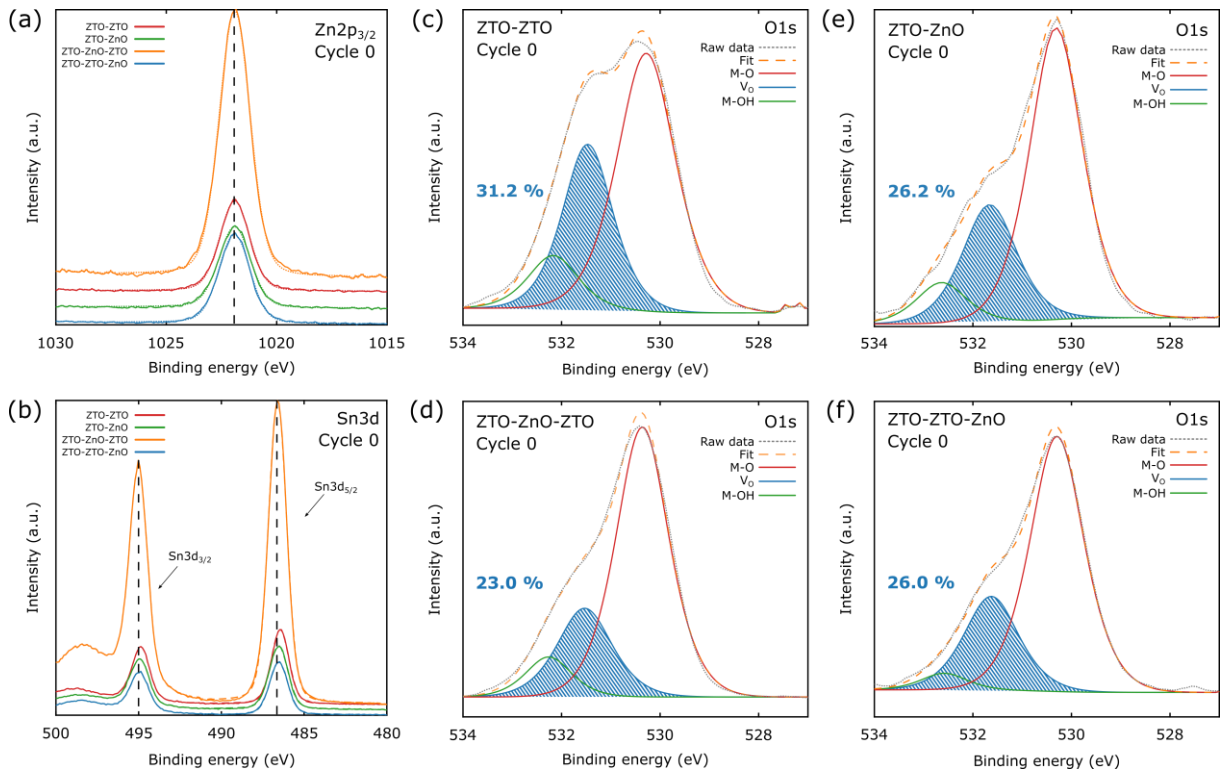


Figure 4. XPS core level spectra of (a) Zn 2p_{3/2} and (b) Sn 3d. XPS core level spectra of (c)-(f) O 1s for ZTO-ZTO, ZTO-ZnO-ZTO, ZTO-ZnO & ZTO-ZTO-ZnO films, respectively.

The presence of oxygen vacancies is commonly regarded as a major factor in the generation and separation of charge carriers within ZnO-based films. Interestingly, high oxygen vacancy content in metal oxides can also promote the adsorption of relevant gases and accommodate more chemisorbed oxygen species that enhance sensitivity and shorten the response time for VOC detection.^[21] Therefore, we conducted an in-depth analysis of the O 1s peak in our metal oxide systems to couple oxygen vacancy content with the electronic properties, so that the most appropriate films could be taken forward as chemiresistive gas sensors. The O 1s peak was deconvoluted into three components through Gaussian–Lorentzian fitting, shown in **Figures 4(c)-(f)**. The lower binding energy component at 530.3 eV was associated with the oxygen bonded to metal atoms (M-O),^[41] while the higher binding energy component at 531.5 eV corresponded to an oxygen-deficient region, related to oxygen vacancy content (V_O) in the metal oxide thin films.^[28] Finally, the component centered at 533.4 eV was ascribed to the presence of loosely bound oxygen, such as hydroxide (M-OH).^[43] The ZTO-ZnO-ZTO film contained the largest proportion of M-O = 70.1 % (**Table S4**), responsible for the high density observed from XRR analysis, while the ZTO-ZTO film contained the lowest percentage of M-O = 57.8 %. However, **Figure 4(c)** shows that the shape of the O 1s envelope for this film was significantly different to the other systems, with a large shoulder created by the large content fraction associated with oxygen vacancies. The ZTO-ZTO film contained the largest proportion of V_O = 31.2 %. In addition, **Table S4** further lists that the ZTO-ZTO film comprised the largest proportion of M-OH = 11.4 %, which could act as additional adsorption sites. On the other hand, the ZTO-ZnO-ZTO film comprised little M-OH = 3.9 %.

The improved electrical performance of the metal oxide TFTs can be primarily attributed to more charge carrier generation by Sn. We also consider that the rougher active layer surface and larger particle size due to the growth of Zn single crystals heavily impacts the charge transport between source-drain electrodes, hence, the ZTO-capped TFTs exhibit superior switching properties compared to the ZnO-capped TFTs. They also show near-zero V_{th} , making them ideal candidates for VOC detection within a low-voltage window. Therefore, the ZTO-ZTO TFT was taken forward and tested for VOC detection. The TFT was exposed to methanol to provide a benchmark sensor response since it possessed the highest oxygen vacancy content. The ZTO-ZTO film also contained the highest M-OH states, which was expected to encourage

high responsivity toward methanol specifically, due to the presence of the hydroxyl groups. To qualitatively assess the specificity of the ZTO-ZTO TFT to methanol, its chemiresistive responses following overnight exposure to other VOCs, specifically acetone, IPA, and toluene, were tested.

2.3. Detection of VOCs in the Air using ZTO-ZTO TFTs

The ZTO-ZTO TFT treated at 500 °C was exposed to methanol vapor overnight to quantify its performance as a chemiresistive gas sensor. These experiments were conducted in a maintained cleanroom environment under controlled conditions (Class 1000, RH = 45.5 %, T = 19.2 °C) in the air i.e., not inside a N₂ glovebox. **Figure 5(a)** shows that V_{th} and $I_{ds[max]}$ increased after exposure, which suggested a decrease in the electrical resistance of the film during adsorption and desorption of gas molecules on the surface. The chemiresistive response (R) of the ZTO-ZTO TFT was calculated by measuring the relative change in I_{ds} (**Equation 5**). Changes in the position at which maximum responsivity was achieved relied upon the V_{gs} at the minimum drain-source current, $I_{ds[min]}$, prior to V_{th} (see **Figure 5(a), (c)**). The magnitude of the maximum responsivity attained was also governed by the $I_{on/off}$ of the as-prepared TFTs, respectively. In this case, $I_{ds[min]}$ of the as-prepared ZTO-ZTO TFT was measured at $V_{gs} = -1.50$ V and maximum responsivity ($R = 1.08 \times 10^6$) was also achieved at this point. The electronic parameters for the as-prepared TFTs as well as after exposure and recovery with heat treatment are summarized in **Table 2**. As it can be observed, the recovery of the device is almost complete after desorption of methanol for 15 minutes since all of the metrics return to values close to those prior to exposure. This indicates that our TFT sensors were very reliable, which is paramount for this type of application.

Table 2. Electrical properties for $L = 80$ μm obtained before and after the ZTO-ZTO TFTs treated at 500 °C were exposed to methanol in the air overnight.

	$I_{on/off}$	V_{th} [V]	μ [cm ² V ⁻¹ s ⁻¹]	μ_{eff} [cm ² V ⁻¹ s ⁻¹]
Before exposure	10 ⁷	3.14	5.21	4.66
Methanol	10 ⁵	-23.3	8.90	8.62
Recovery	10 ⁶	2.63	5.48	4.95

To further assess our ZTO-ZTO sensor's reliability and reproducibility, its dynamic response, shown in **Figure 5(b)**, was measured following short (1 hour), long (4 hours) and overnight (24 hours) exposure periods. The ZTO-ZTO TFT was recovered with heat treatment for 15 minutes as previously described after each exposure cycle (cyan lines).

To confirm our specificity to vapors that contain the -OH hydroxyl group, we exposed the ZTO-ZTO TFT to acetone, IPA, and toluene. Toluene, a subclass of VOCs with aromatic rings, can serve as an important biomarker for cancer. Indeed, abnormally high concentrations of toluene have been observed in the exhaled breath of patients with lung cancer compared to healthy non-smokers^[44]. The good specificity of a sensor for aromatic compounds like toluene depends chiefly on the previously mentioned chemical environment of the sensing material, the decomposition rate of the adsorbed molecule on the surface and operation temperature. The calculated responsivity following overnight exposure shown in **Figure 5(c)** (24 h, solid purple lines) far surpassed that measured for acetone, IPA, and toluene vapors. In fact, our ZTO-ZTO TFT was more responsive ($R = 11,400$) after exposure to methanol for 4 hours (**Figure 5(c)** inset, dashed purple lines) compared with overnight exposure to acetone ($R = 9,330$). Our ZTO-ZTO TFT sensors were highly specific to vapors that contain the -OH hydroxyl group because of their high oxygen vacancy and M-OH bonding contents, which acted as specific adsorption sites. It is inferred that the methanol vapor adsorbed on the ZTO-ZTO surface more easily than IPA owing to its much lower vapor pressure, size, and molecular weight. In contrast, the responsivity signature obtained following exposure to acetone was much less, possibly due to the reduced polarity of the -C=O carbonyl group. Now, **Figures 5(d)** show that the relative change in I_{ds} after overnight exposure to toluene at room temperature was negligible, which alluded that the toluene vapor, specifically the methyl group, was less prone to adsorption and desorption on the ZTO-ZTO surface compared to the other reducing vapors.

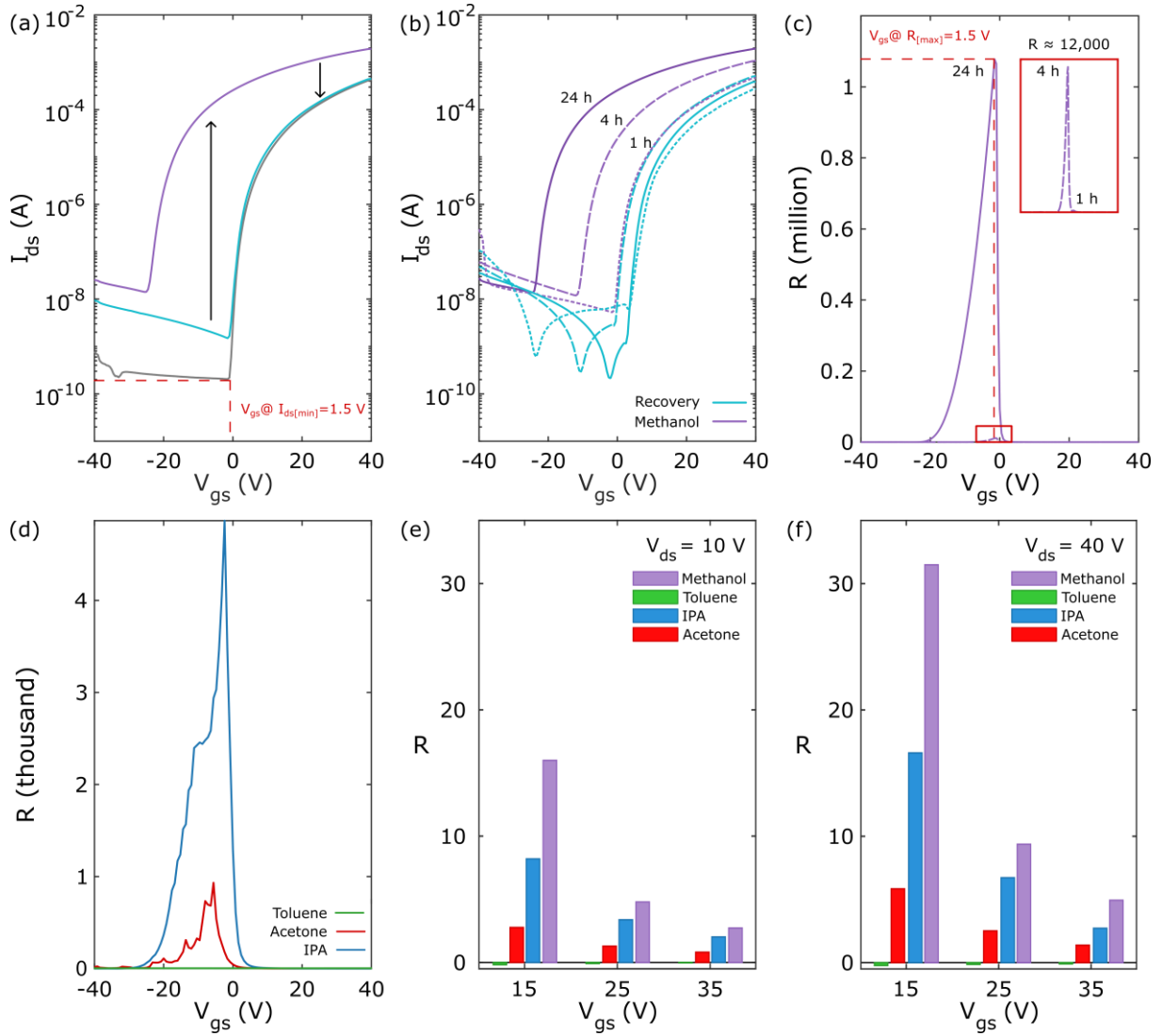


Figure 5. (a) Transfer characteristics in the saturation regime at $V_{ds} = 40$ V, $V_{gs} = -40$ to 40 V and $L = 80$ μm following overnight exposure to methanol vapor and recovery with heat treatment. (b) Dynamic sensor response and (c) calculated responsivity following 1 hour, 4 hours (inset, dashed purple lines) and 24 hours exposure periods. (d) Calculated responsivity following overnight exposure to toluene, acetone, and IPA vapors. (e) Transient sensor response at fixed $V_{gs} = 15$ V, 25 V and 35 V in the linear and (f) saturation regimes.

Finally, **Figures 5(e)-(f)** show the transient responses of the ZTO-ZTO TFT at fixed $V_{gs} = 15$ V, 25 V and 35 V in the linear and saturation regimes, $V_{ds} = 10$ V and 40 V, respectively. In both regimes, responsivity is maximized as V_{gs} approaches the V_{th} of the as-prepared TFTs following exposure to oxygen-related VOCs: acetone, IPA, and methanol. The ZTO-ZTO TFT was clearly more sensitive to these vapors in the saturation regime, governed by **Equation 1**.

Methanol underwent a redox reaction with adsorbed oxygen on the ZTO-ZTO surface (**Equations 6-7**, supporting information).^[18,40] Due to the large electronegativity of oxygen atoms, adsorbed oxygen depleted electrons from the metal oxide film during thermal treatment, which increased its resistance and formed reduced oxygen species at room temperature.^[45,46] The high density of oxygen vacancies in the ZTO-ZTO film acted as acceptors of oxygen ion species in ambient conditions, creating a thicker depletion layer. Increased charge density in the vicinity of the valence band maximum and conduction band minimum. due to these oxygen vacancies, possibly narrows the bandgap, which may have favored the adsorption of target gas molecules.^[21,47] Specific sites for the adsorption of hydroxyl groups also means that methanol molecules interact with a greater number of oxygen ion species leading to a significant increase in I_{ds} , which is consistent with free electrons being released back into the conduction band. These changes resulted primarily from the reduction reaction with adsorbed oxygen on the ZTO-ZTO film surface and were unaffected by the presence of grain boundaries because of the amorphous nature of the layer.^[7] The difference in sensing characteristics suggested that ZTO-ZTO TFTs could achieve accurate cross-sensitivity toward exhaled breath containing multiple gases and high responsivity at the V_{gs} required for a battery-driven chemiresistive gas sensor.

3. Conclusion

To conclude, the electrical performance of ZTO-based TFTs has been tailored by adopting a ZTO and ZnO multilayering design strategy for improved chemiresistive response. The addition of a ZnO layer significantly influenced the crystalline and morphological properties of the metal oxide films. The ZTO-capped TFTs yielded better electrical performance, while a ZnO capping layer caused the growth of ZnO particles, which created a much rougher film surface with worsened source-drain contacts. With this in mind, the ZTO-ZTO TFT achieved near-zero threshold voltage ($V_{th} = 2.20$ V) and excellent switching properties ($I_{on/off} = 10^7$) while maintaining high mobility ($\mu_{eff} \approx 10$ cm²V⁻¹s⁻¹). Its low surface roughness, superb Zn and Sn intermixing, high oxygen vacancy (31.2 %) and M-OH bonding (11.4 %) contents shows that this TFT was deemed an ideal chemiresistive sensor and subsequently exposed to a variety of VOCs with different functional groups, specifically acetone, IPA, methanol, and toluene. Our qualitative analyses demonstrated a high responsivity to alcohol vapors at low-voltage operation with peak responsivity for methanol ($R = 1.08 \times 10^6$) over two orders of magnitude greater than acetone. We have shown that the chemical environment influences the carrier transport properties of ZTO-based TFTs and can be tailored toward the detection of specific

VOCs, ensuring that high specificity can be achieved for the diagnosis of life-threatening conditions by simple breath analysis.

4. Experimental Section/Methods

Transistor Fabrication: The substrates consisted of a 400 nm SiO₂ dielectric on a highly doped Si wafer, which acted as the back gate. They were cleaned by sonication in acetone and IPA ($\geq 99.5\%$ from Sigma-Aldrich) separately for 15 minutes to remove debris, fibers or inorganic contaminants and blow-dried with N₂. Finally, they were placed in a UV ozone cleaner (Novascan) for 1 hour to remove oils, fingerprints, or organic contaminants. This process also increased the wettability of the substrates prior to spin-coating and ensured that a uniform layer of material was deposited with the desired thickness. The precursor solutions were prepared under a fume hood. ZnCl₂ and SnCl₂ (150 mM, anhydrous, 99.999% from Sigma-Aldrich) powders were dissolved in 2-methoxyethanol separately and sonicated for 15 min. The ZTO solution was prepared by mixing equal amounts of ZnCl₂ and SnCl₂ (1:1) precursor solutions and was aged under stirring for 24 h at room temperature. The ZTO and ZnO solutions were filtered through a syringe filter (0.42 μm) and spin-coated onto the cleaned substrates under a fume hood. The multilayer films were grown by the sequential deposition and thermal treatment of ZTO and ZnO at temperatures in the range of 300-500 °C. After deposition and thermal treatment, 50 nm thick Al source-drain electrodes were deposited via thermal evaporation using a shadow mask under high vacuum ($\approx 10^{-6}$ mbar) in an evaporation chamber integrated within a N₂ glovebox.

Characterization and Measurements: The electrical characterization of the TFTs was performed in ambient conditions using two Agilent B2912A semiconductor parameter analyzers. Our bespoke chamber (**Figure S11**) was manufactured to record changes in transfer characteristics upon exposure to reducing vapors.

The thermal behaviour of the ZTO, ZnO and SnO₂ solutions was examined using thermal gravimetric analysis (TGA) (Perkin Elmer Pyris 1 TGA) at a heating rate of 10 °Cmin⁻¹ from 30 °C to 500 °C in the air. Data processing was completed using the complementary software package, PyrisTM.

The crystalline properties of the films were determined using XRD and XRR (Bruker AXS D8 Advance GX003410). Surface morphology was examined by AFM (Asylum Research MFP-

3D Infinity). Image processing and analysis were performed using the open-source software Gwyddion.

The chemical states of the metal oxide films were examined using XPS surface and depth profiling analyses. XPS measurements were carried out in a SPECS ProvenXPS system equipped with a PHOIBOS 150 2D-CMOS hemispherical analyzer and a monochromatic X-ray source FOCUS 500. The Al K α X-ray source (1486.6 eV) operated at 400 W and was separated from the analyzer by 55 °. A medium magnification mode and constant pass energy of the analyzer equal to 20 eV were used for analysis. Photoelectron data were recorded at a take-off angle of 90 ° (normal detection). The survey spectrum and the high-resolution spectra were recorded with an energy step of 0.5 eV over 1400 eV and 0.1 eV, respectively. Binding energies, line widths and areas of the different XPS peaks were obtained by a weighted least-squares fitting of a Gaussian-Lorentzian model curve to the experimental data using the program CasaXPS. For depth profiling analyses, the samples were etched using an Ar ion gun at 2 keV with a sample current density of 0.5 μAcm^{-2} . The etch cycle duration was 60 s, and the rate was approximated as $0.025 \pm 0.05 \text{ nms}^{-1}$. The atomic concentrations were calculated assuming that the analysed depth was homogeneous.

Field emission SEM (FESEM) images of the ZTO-ZTO-ZnO and ZTO-ZnO-ZTO films were obtained by using a FEI Helios Nanolab 600 at 15 kV. High-resolution TEM (HRTEM) and energy-dispersive X-ray spectroscopy (EDX) were carried out in a JEOL 2100F FEG at 200 kV, equipped with an Oxford Instruments Aztec microanalysis system. The cross-sectional samples were prepared in the FESEM system, equipped with a Ga focused ion beam (FIB) source. Pt was deposited on the films prior to FIB milling to ensure a smooth and clean cross-section was obtained.

Calculation of Effective Mobility: Assuming that μ is independent of V_{gs} and neglecting short channel effects, I_{ds} in the saturation regime is given by **Equation 1**.^[48]

$$I_{ds} = \frac{WC_i}{2L} \mu (V_{gs} - V_{th})^2, \quad (1)$$

where I_{ds} is the drain current, $\frac{W}{L}$ is the channel width-to-length ratio, C_i is the capacitance per unit area of the dielectric layer, μ is the charge carrier mobility, V_{gs} is the gate voltage and V_{th}

is the threshold voltage. μ is obtained by taking the partial derivative with respect to V_{gs} . Rearranging the resulting equation yields **Equation 2**:

$$\mu = \frac{2L}{WC_i} \left(\frac{\partial \sqrt{I_{ds}}}{\partial V_{gs}} \right)^2. \quad (2)$$

$\frac{\partial \sqrt{I_{ds}}}{\partial V_{gs}}$ can be extracted by plotting $\sqrt{I_{ds}}$ against V_{gs} and finding the gradient. Ideal transfer characteristics are linear and hence $\frac{\partial \sqrt{I_{ds}}}{\partial V_{gs}}$ is constant. In practice, external factors such as contact resistance can produce curved plots, which has resulted in several erroneous reported mobilities. The reliability factor (r) given in **Equation 3** accounts for nonlinearities in transfer characteristics.^[48] It is defined as the ratio (expressed in %) of the maximum channel conductivity experimentally achieved in a FET to that calculated in an equivalent ideal FET:

$$r = \frac{\left(\frac{\sqrt{|I_{ds}|^{max}} - \sqrt{|I_{ds}|^0}}{|V_{gs}|^{max}} \right)^2}{\left(\frac{WC_i}{2L} \mu \right)_{claimed}^2}, \quad (3)$$

where $\left(\frac{WC_i}{2L} \mu \right)_{claimed}^2$ accounts for the claimed device parameters and mobility in the saturation regime. $|I_{ds}|^{max}$ is the experimental maximum drain current reached at the maximum gate voltage, $|V_{gs}|^{max}$. $|I_{ds}|^0$ is the drain current at $V_{gs} = 0$. Effective mobility, μ_{eff} , is thus given by:

$$\mu_{eff} = \mu \times r. \quad (4)$$

The values quoted in this report are μ_{eff} and calculated using $C_i = 9 \text{ nFcm}^{-2}$ and $W = 3 \text{ mm}$. $L = 80 \text{ }\mu\text{m}$ unless otherwise stated.

Calculation of Responsivity: The chemiresistive responses of the TFT gas sensors were measured using our sealed custom-built testing rig shown in **Figure S11**. An open 3 mL vial was filled with solvent and placed in the chamber, which was allowed to evaporate overnight to ensure that the sensor was saturated with the target vapor. The TFT was retested before the taps on the chamber were opened in a fume cupboard. Afterwards, it was removed and heated at $100 \text{ }^\circ\text{C}$ for 15 minutes to recover I_{ds} . In general, the sensitivity of conventional chemiresistive gas sensors has been expressed as a ratio of resistance or drain current variation. R was calculated using:^[18,19,49]

$$R = \frac{\Delta I_{ds}}{I_{ds}[0]} = \frac{I_{ds}[gas] - I_{ds}[0]}{I_{ds}[0]}, \quad (5)$$

where ΔI_{ds} represents the difference in I_{ds} before ($I_{ds}[0]$) and following ($I_{ds}[gas]$) exposure to reducing vapors.

Supporting Information

Supporting information is available from the Wiley Online Library or from the author.

Conflicts of Interest

There is no conflict of interest to declare.

Data Availability

The datasets presented during this study are available from the authors on reasonable request.

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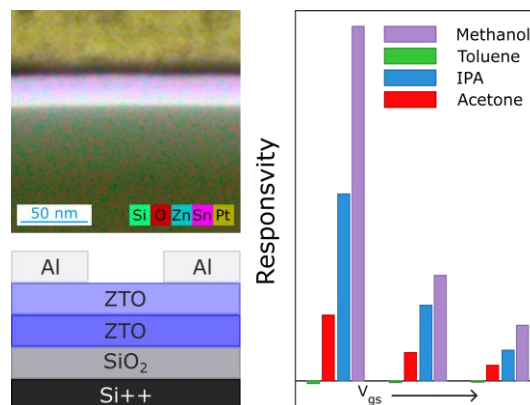
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Control strategies for solution-processed metal oxide thin-film transistors tailored for the detection of volatile organic compounds

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Does my breath smell? We report a major advancement in amorphous Zn-Sn-O-based thin film transistors using a multilayer design. In-depth compositional and morphological analyses provide pathways to achieve outstanding electronic performance. Our solution-processed method demonstrates proof-of-concept for VOC detection, with significant potential for diagnosing life-threatening medical conditions through non-invasive exhaled breath analysis (see picture).



Supporting Information

Control strategies for solution-processed metal oxide thin-film transistors tailored for the detection of volatile organic compounds

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Table S1. Electrical properties obtained from ZTO-based TFTs treated at 500 °C and prepared from 0.3 M and 0.15 M precursor solutions.

Table S2. Electrical properties obtained from ZTO-ZTO TFTs treated at temperatures from 300 °C to 500 °C.

Table S3. Summary of the fitting parameters namely, layer thickness, SLD and interface width used to fit the experimental XRR spectra for each system studied. The metal oxide systems were simulated assuming a smooth and continuous surface.

Table S4. Percentage contents and position of O 1s components for bilayer and trilayer films.

Table S5. Atomic concentration (%) and calculated composition ratios at etch cycle five following XPS depth profiling of bilayer and trilayer films.

Table S6. Electrical properties for $L = 80\ \mu\text{m}$, $100\ \mu\text{m}$ & $120\ \mu\text{m}$ obtained before and after the ZTO-ZTO TFTs treated at $500\ ^\circ\text{C}$ were exposed to IPA in the air.

Table S7. Electrical properties for $L = 80\ \mu\text{m}$, $100\ \mu\text{m}$ & $120\ \mu\text{m}$ obtained before and after the ZTO-ZTO TFTs treated at $500\ ^\circ\text{C}$ were exposed to acetone in the air.

Table S8. Electrical properties for $L = 80\ \mu\text{m}$, $100\ \mu\text{m}$ & $120\ \mu\text{m}$ obtained before and after the ZTO-ZTO TFTs treated at $500\ ^\circ\text{C}$ were exposed to toluene in the air.

Table S9. Comparison of the TFT-based gas sensors' performance.

Figure S1. (a) Output characteristics at $V_{\text{ds}} = 0$ to $40\ \text{V}$ and $V_{\text{gs}} = 0$ to $40\ \text{V}$ for ZTO-ZTO TFTs treated at $500\ ^\circ\text{C}$ and (b) $450\ ^\circ\text{C}$. Transfer characteristics in the saturation regime at $V_{\text{ds}} = 40\ \text{V}$ and $V_{\text{gs}} = -20$ to $40\ \text{V}$ for the ZTO-ZTO TFTs treated at temperatures from $300\ ^\circ\text{C}$ to $500\ ^\circ\text{C}$.

Figure S2. Individual elemental mapping of the (a)-(e) ZTO-ZTO-ZnO and (f)-(j) ZTO-ZnO-ZTO films.

Figure S3. AFM image ($1\ \mu\text{m}^2$ scan area) of (a) ZTO (b) ZTO-ZTO and (c) ZTO-ZnO films with calculated rms surface roughness.

Figure S4. SEM images of the (a) ZTO-ZnO-ZTO and (b) ZTO-ZTO-ZnO thin films. (c) High magnification images of the ZTO-ZTO thin film and (d) calculated thickness from a cross-section.

Figure S5. XPS wide scan of (a)-(b) ZTO-ZTO and (c)-(d) ZTO-ZnO films at etch cycles zero and twenty.

Figure S6. XPS wide scan of (a)-(b) ZTO-ZTO-ZnO and (c)-(d) ZTO-ZnO-ZTO films at etch cycles zero and twenty.

Figure S7. XPS depth profile of (a) ZTO-ZTO (b) ZTO-ZnO (c) ZTO-ZTO-ZnO and ZTO-ZnO-ZTO films.

Figure S8. Transfer characteristics in the saturation regime at $V_{\text{ds}} = 40\ \text{V}$, $V_{\text{gs}} = -40$ to $40\ \text{V}$ and $L = 80\ \mu\text{m}$, $100\ \mu\text{m}$ & $120\ \mu\text{m}$, obtained before and after the ZTO-ZTO TFTs treated at $500\ ^\circ\text{C}$ were exposed separately to (a) acetone, (b) IPA and (c) toluene in the air.

Figure S9. Transfer characteristics for the ZTO-ZTO TFTs treated at $500\ ^\circ\text{C}$ in the saturation regime at $V_{\text{ds}} = 40\ \text{V}$, $V_{\text{gs}} = -40$ to $40\ \text{V}$ and $L = 80\ \mu\text{m}$ following overnight exposure to (a)

IPA, (b) acetone and (c) toluene vapors. Recovery with heat treatment is shown by the solid cyan lines.

Figure S10. Transfer characteristics in the saturation regime at $V_{ds} = 40$ V, $V_{gs} = -40$ to 40 V and $L = 80$ μm for the ZTO-ZnO TFTs treated at 500 °C following overnight exposure to (a) IPA and (b) acetone vapors. (c) Calculated responsivity. (d) Transient sensor response at fixed $V_{gs} = 15$ V, 25 V and 35 V in the linear and (e) saturation regimes.

Figure S11. Bespoke testing chamber with device stage illustrations corresponding to source-drain electrode shadow mask.

Electronic performance of ZTO TFTs prepared from a highly concentrated precursor solution

To highlight the benefit of controlling film thickness and morphology via the sequential spin-casting and thermal treatment of metal oxide layers, the electronic performance of a single layer ZTO TFT prepared from a precursor solution with double the concentration (0.3 M) was compared against the ZTO-ZTO TFT presented in **Figure 1**. This would equate to the same amount of metal oxide content as the two stacked ZTO layers. A summary of the electrical parameters is given in **Table S1**.

We have shown that the ZTO TFT prepared from a more concentrated precursor solution performed poorly. μ_{eff} was almost two orders of magnitude lower and V_{th} over twice as high in comparison to the ZTO-ZTO TFT.

Table S1. Electrical properties obtained from ZTO-based TFTs treated at 500 °C and prepared from 0.3 M and 0.15 M precursor solutions.

Device	Concentration (M)	$I_{\text{on/off}}$	V_{th} [V]	μ [cm ² V ⁻¹ s ⁻¹]	μ_{eff} [cm ² V ⁻¹ s ⁻¹]
ZTO ZTO	0.15	10 ⁷	2.20	10.2	9.49
ZTO	0.30	10 ⁶	4.78	0.172	0.159

Thermal treatment of ZTO-ZTO TFTs

The TGA of the precursors (**Figure 1(b)**) revealed a weight reduction prior to 200 °C that could have been attributed to the evaporation of the organic solvent, 2-methoxyethanol, which has a boiling point of 124 °C. For the SnO₂ precursor, there was a phase transition from SnCl₂ to SnO₂ between 300 °C and 450 °C. No further weight loss was recorded after 450 °C, however, changes were still observed up to 500 °C for the ZnO precursor. Therefore, the ZTO films were treated at 500 °C to assess the impact of thermal treatment on the properties of ZTO-based TFTs and the temperature of the hot plate did not exceed 500 °C to ensure that our fabrication process remained low-cost. V_{th} shifted towards positive bias with increasing temperature, reaching a near-zero value at 500 °C. In addition, $I_{on/off}$ drastically improved from $< 10^2$ at 300 °C to $> 10^7$ for the TFT treated at 500 °C. In particular, this TFT exhibited a very high mobility of $\mu_{eff} = 9.49 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$, far surpassing that achieved by those treated at lower temperatures (see **Table S2**). It is inferred that the suppression of residual chloride species during the phase transitions of the precursor solution could have led to the remarkable enhancement of device performance.^[50–52]

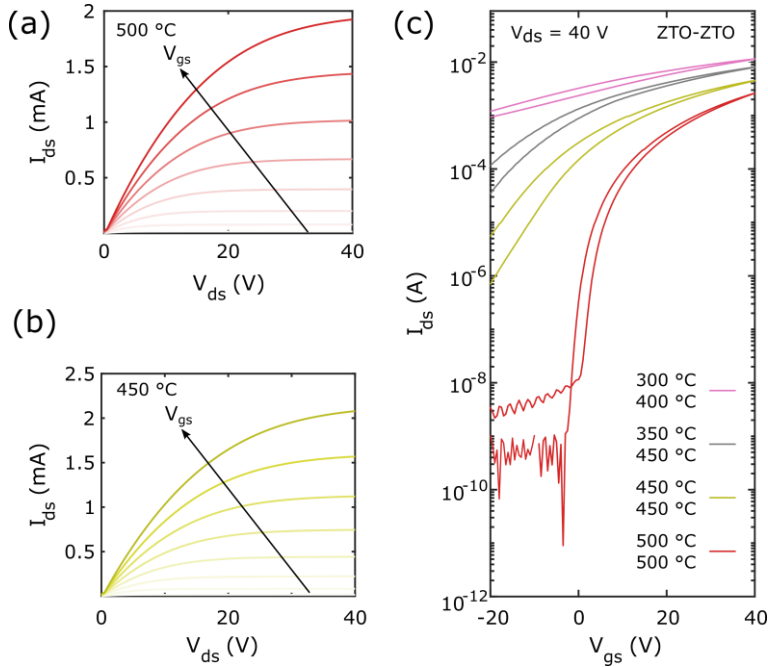


Figure S1. (a) Output characteristics at $V_{ds} = 0$ to 40 V and $V_{gs} = 0$ to 40 V for ZTO-ZTO TFTs treated at 500 °C and (b) 450 °C. Transfer characteristics in the saturation regime at $V_{ds} = 40$ V and $V_{gs} = -20$ to 40 V for the ZTO-ZTO TFTs treated at temperatures from 300 °C to 500 °C.

Table S2. Electrical properties obtained from ZTO-ZTO TFTs treated at temperatures from 300 °C to 500 °C.

Temperature [°C]	$I_{\text{on/off}}$	V_{th} [V]	μ [cm ² V ⁻¹ s ⁻¹]	μ_{eff} [cm ² V ⁻¹ s ⁻¹]
300 400	10^2	-45.4	9.42	9.33
350 450	10^4	-27.8	10.6	10.5
450	10^6	-13.6	9.39	9.00
500	10^7	2.20	10.2	9.49

Calculation of XRR spectra

Table S3. Summary of the fitting parameters namely, layer thickness, SLD and interface width used to fit the experimental XRR spectra for each system studied. The metal oxide systems were simulated assuming a smooth and continuous surface.

Film	Layer	Thickness [Å]	SLD [$\text{r}_e\text{Å}^{-3}$]	Interface width [Å]
ZTO	SiO ₂	N/A	0.0804	4.60
	ZTO	76.6	1.15	11.6
ZTO ZTO	SiO ₂	N/A	0.0804	9.68
	ZTO	74.6	1.26	5.86
	ZTO	54.4	1.15	8.42
ZTO ZnO	SiO ₂	N/A	0.0804	14.3
	ZTO	154.9	1.26	4.76
	ZnO	10.8	0.953	20.1
ZTO ZnO ZTO	SiO ₂	N/A	0.0804	10.2
	ZTO	84.1	1.59	8.17
	ZnO	55.2	1.46	5.25
	ZTO	2.46	2.78	7.35
ZTO ZTO ZnO	SiO ₂	N/A	0.0804	10.8
	ZTO	77.3	1.48	7.73
	ZTO	78.7	1.34	5.44
	ZnO	3.43	1.95	8.86

Elemental and morphological analyses of the solution-processed trilayer metal oxide systems.

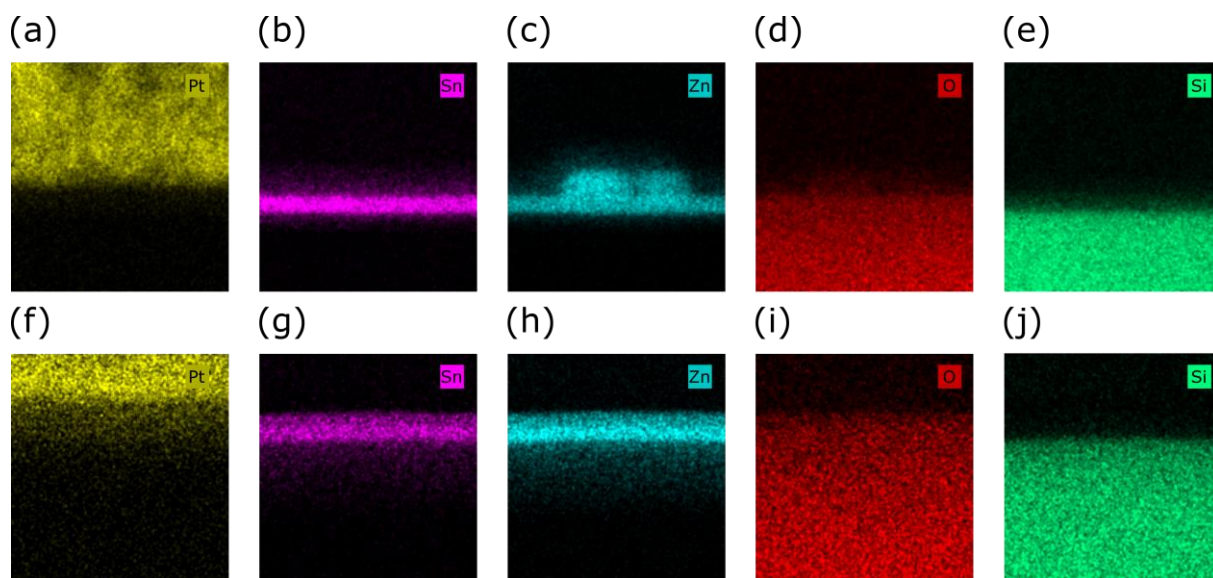


Figure S2. Individual elemental mapping of the (a)-(e) ZTO-ZTO-ZnO and (f)-(j) ZTO-ZnO-ZTO films showing the Pt, Sn, Zn, O and Si components from left to right. These maps are overlapped to produce **Figures 3(b)** and **3(g)**. Oxygen was present throughout both samples. Pure Zn features were found on top of the initial ZTO base layer for the ZTO-ZTO-ZnO film. Similar concentrations of Sn and Zn were observed for ZTO-capped trilayer film.

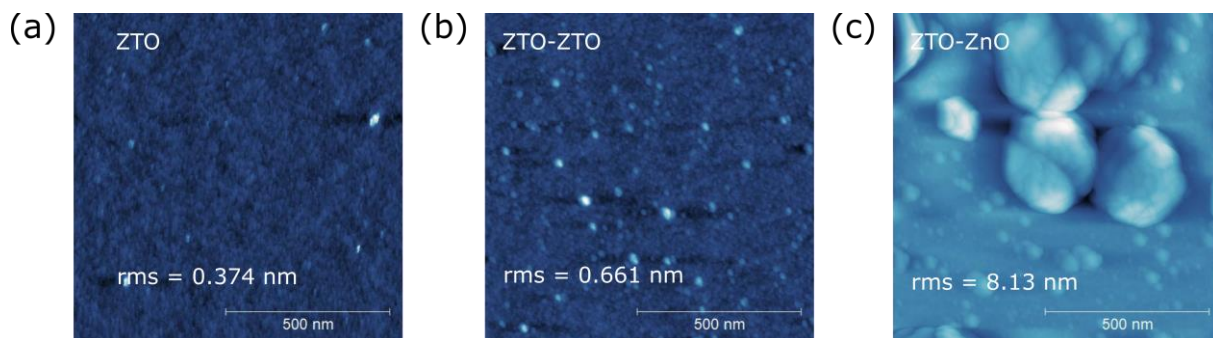


Figure S3. AFM image ($1\ \mu\text{m}^2$ scan area) of (a) ZTO (b) ZTO-ZTO and (c) ZTO-ZnO films with calculated rms surface roughness. The ZTO-capped films displayed high-quality amorphous morphology. The monolayer film had a surface roughness comparable to that of the Si substrates ($< 5\ \text{\AA}$). The ZTO-ZnO sample clearly showed crystalline features, which contributed to a rougher surface, in-line with the alternate ZnO-capped trilayer film presented in **Figure 3(h)**.

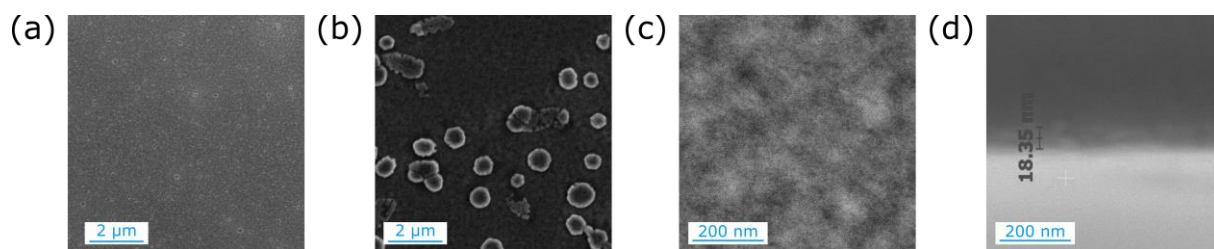


Figure S4. SEM images of the (a) ZTO-ZnO-ZTO and (b) ZTO-ZTO-ZnO thin films. (c) High magnification images of the ZTO-ZTO thin film and (d) calculated thickness from a cross-section.

XPS surface and depth profiling analyses

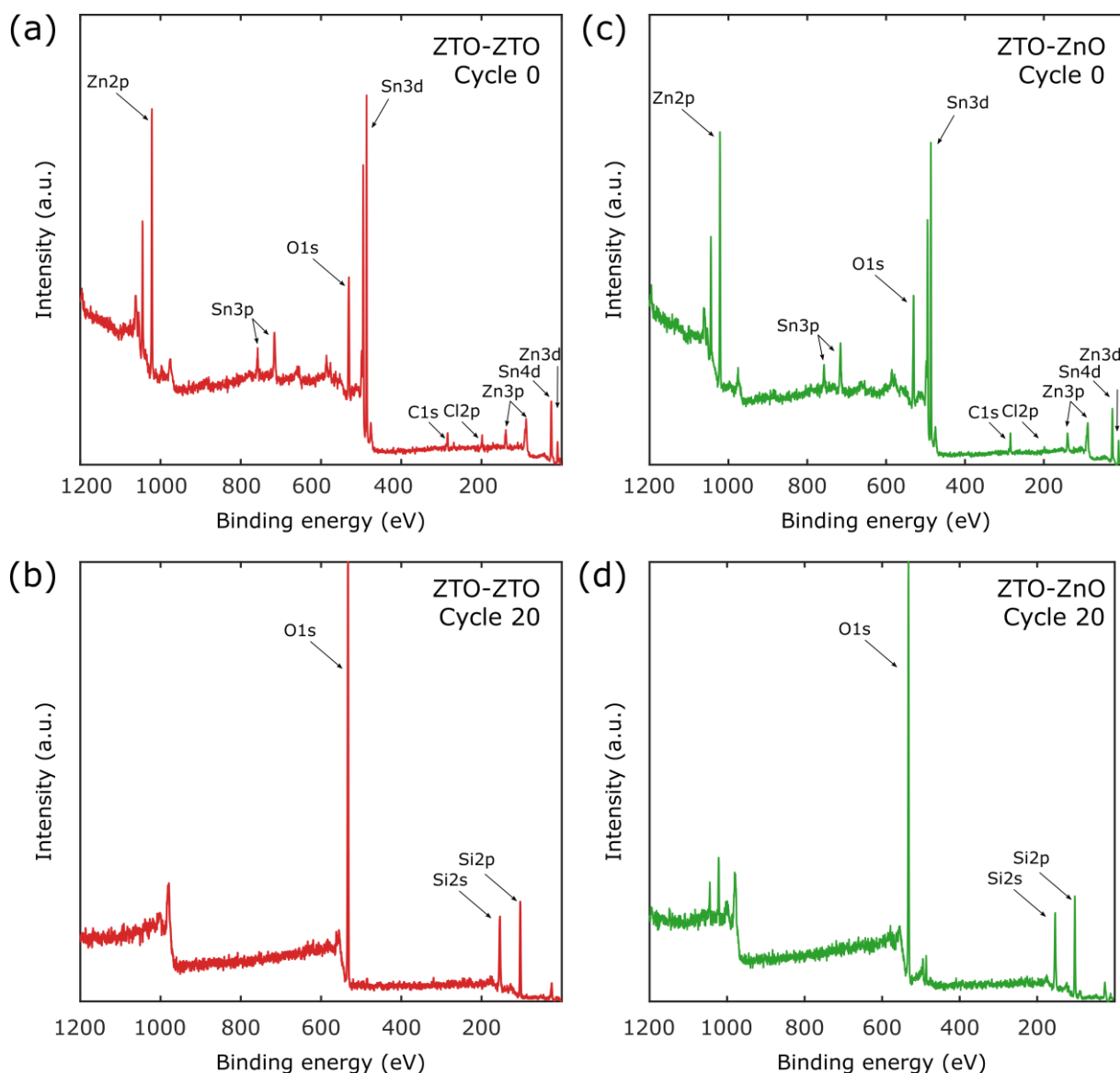


Figure S5. XPS wide scan of (a)-(b) ZTO-ZTO and (c)-(d) ZTO-ZnO films at etch cycles zero and twenty. Little Cl species was present owing to thermal treatment at 500 °C. The intensities of the O 1s, Si 2s and Si 2p components were amplified moving from etch cycle zero to twenty as the ion beam approached the surface of the substrate. The Zn 2p signal was still prominent at etch cycle twenty for the ZTO-ZnO sample only in-line with the depth profiling presented in **Figure 2(d)**.

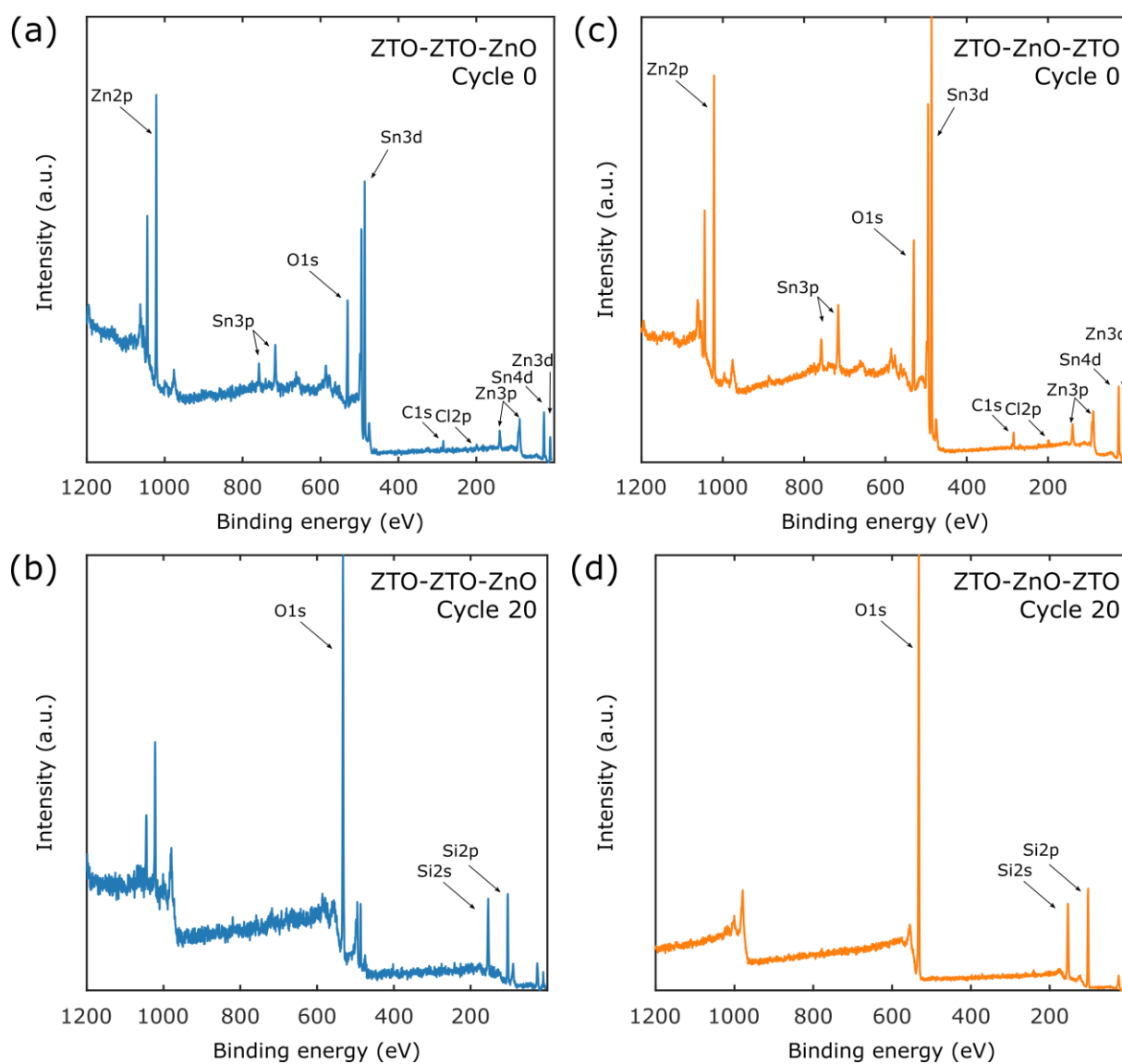


Figure S6. XPS wide scan of (a)-(b) ZTO-ZTO-ZnO and (c)-(d) ZTO-ZnO films at etch cycles zero and twenty. The Zn 2p peak was present at the surface of the substrate for the ZnO-capped film, similarly to that shown for the ZTO-ZnO film.

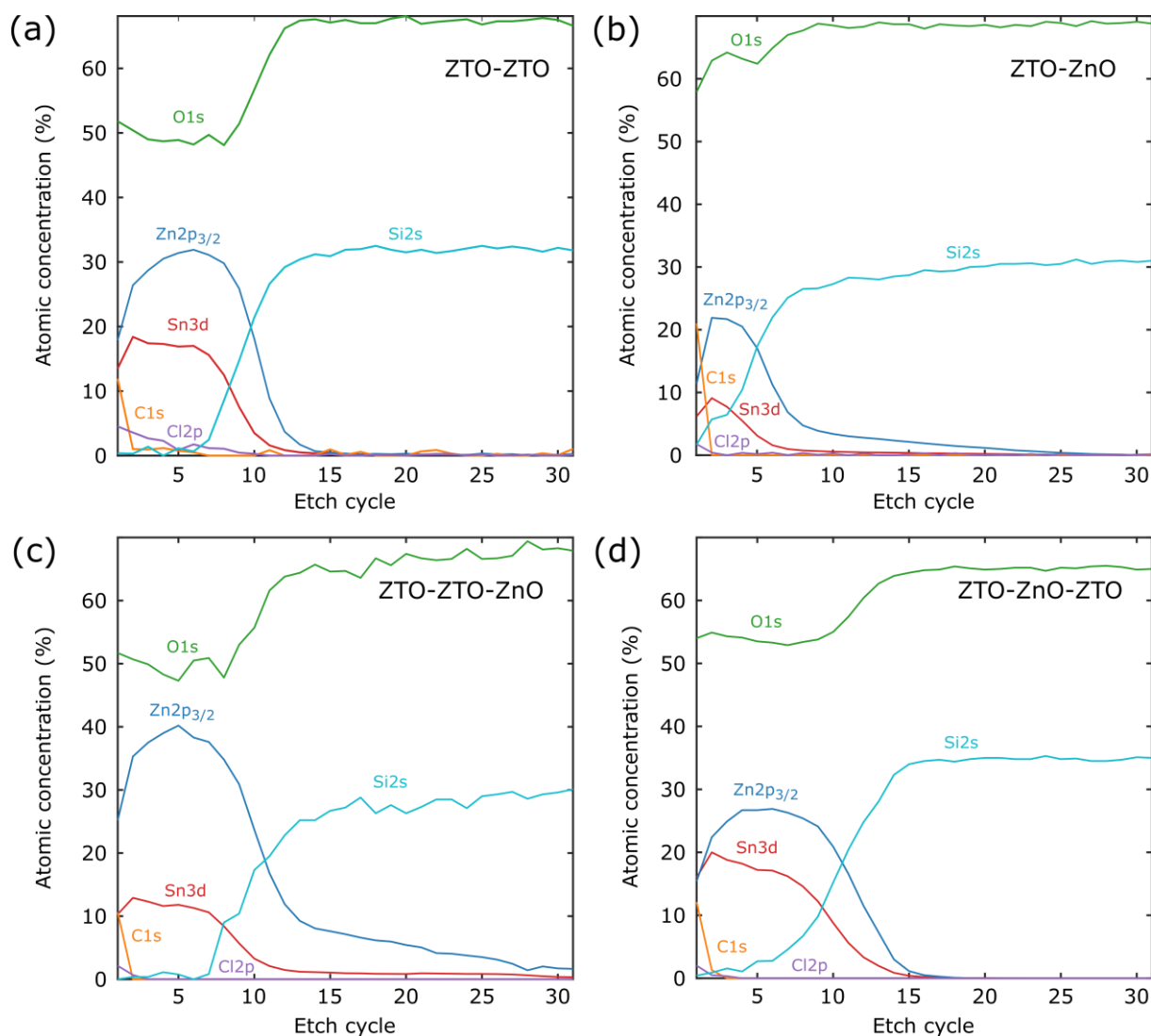


Figure S7. XPS depth profile of (a) ZTO-ZTO (b) ZTO-ZnO (c) ZTO-ZTO-ZnO and ZTO-ZnO-ZTO films. The atomic concentrations described proceeding **Figure 4** were taken at etch cycle five as the Zn 2p and Sn 3d signals were most obvious. The C 1s and Cl 2p signals were diminished in all cases.

Table S4. Percentage contents and position of O 1s components for bilayer and trilayer films.

Film	M-O		V _O		M-OH	
	(%)	(eV)	(%)	(eV)	(%)	(eV)
ZTO ZTO	57.80	530.28	31.16	531.45	11.40	532.13
ZTO ZnO	64.36	530.31	26.24	531.64	9.40	532.58

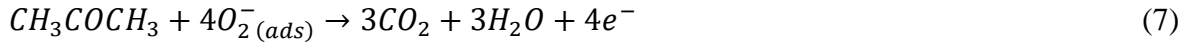
ZTO						
ZTO	68.19	530.36	23.02	531.53	8.79	532.26
ZnO						
ZTO						
ZnO	70.08	530.29	26.01	531.63	3.91	532.58
ZTO						

Table S5. Atomic concentration (%) and calculated composition ratios at etch cycle five following XPS depth profiling of bilayer and trilayer films.

Film	O 1s (%)	Sn 3d (%)	Zn 2p _{3/2} (%)
ZTO			
ZTO	48.90	16.90	31.40
ZTO			
ZnO	62.40	3.09	17.00
ZTO			
ZTO	47.30	11.80	40.20
ZnO			
ZTO			
ZnO	53.50	17.20	26.70
ZTO			

Chemiresistive properties of ZTO-ZTO TFTs

A typical redox reaction between acetone and adsorbed oxygen at room temperature is given below:



Having studied the electrical performance of the ZTO-ZTO TFT previously, we also investigated the effect of source-drain electrode geometry on its electrical and chemiresistive properties to deepen our understanding of the responsivity obtained following exposure to acetone, IPA, and toluene. Subsequently, the channel width was maintained at $W = 1$ mm and the length was varied with $L = 80 \mu\text{m}$, $100 \mu\text{m}$ & $120 \mu\text{m}$. **Figure S8** shows that the maximum drain current ($I_{ds[max]}$) attained by the as-prepared TFTs (solid lines) decreased with increasing channel length, as the resistance of the channel was inversely proportional to the width-to-length ratio (**Equation 1**).

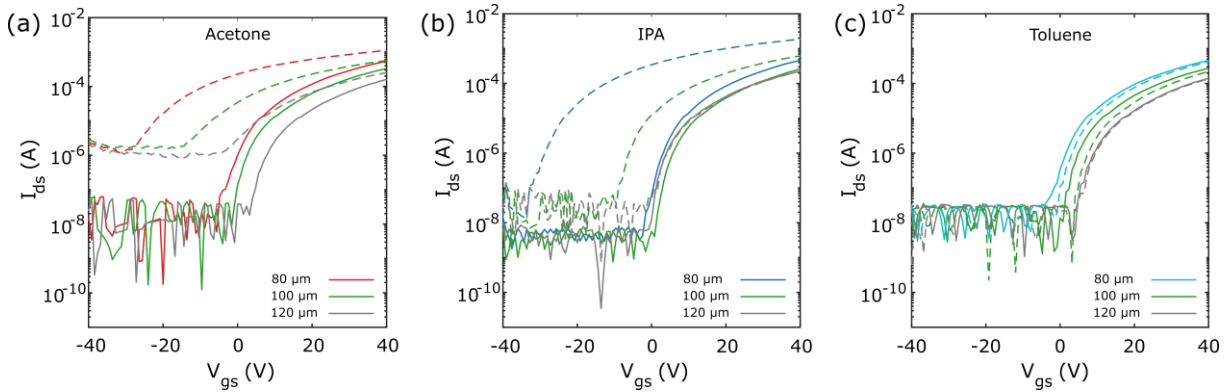


Figure S8. Transfer characteristics in the saturation regime at $V_{ds} = 40$ V, $V_{gs} = -40$ to 40 V and $L = 80 \mu\text{m}$, $100 \mu\text{m}$ & $120 \mu\text{m}$, obtained before and after the ZTO-ZTO TFTs treated at 500°C were exposed separately to (a) acetone, (b) IPA and (c) toluene in the air and at room temperature. The electrical properties declined at larger channel lengths, owing to increased resistance in the channel.

Figures S9(a)-(b) show that the off-current and $I_{on/off}$ of the TFT exposed to IPA vapor was maintained, this contrasts with the sensor exposed to acetone, which led to improved signal-to-noise ratio and responsivity, see **Figure 5(d)**. The peak responsivity of the TFT exposed to IPA vapors was approximately five times greater than that of the TFT exposed to acetone, with V_{gs}

= −5.60 V and −2.40 V, respectively. It is possible that the chemical environment, namely the high proportion of M-OH states, contributed towards $R \approx 50,000$ recorded following exposure to IPA vapor, owing to increased specific adsorption sites for hydroxyl groups (**Table S7**). In both cases, responsivity was maximized within a low-voltage window, determined by the low off-current and near-zero V_{th} of the as-prepared ZTO-ZTO TFTs treated at 500 °C.

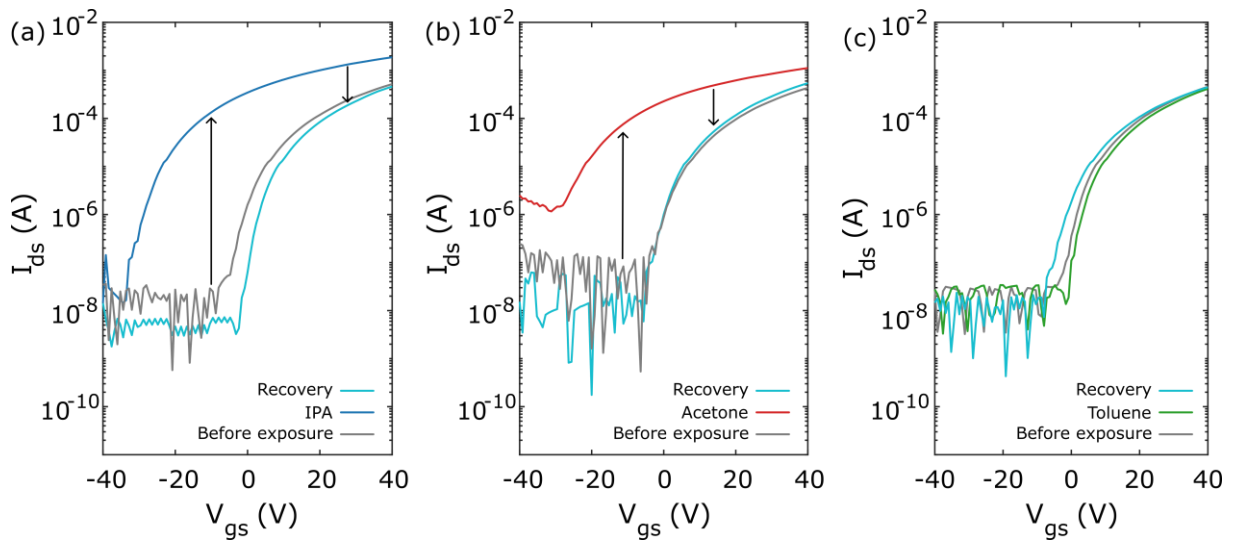


Figure S9. Transfer characteristics for the ZTO-ZTO TFTs treated at 500 °C in the saturation regime at $V_{ds} = 40$ V, $V_{gs} = -40$ to 40 V and $L = 80$ μm following overnight exposure to (a) IPA, (b) acetone and (c) toluene vapors. Recovery with heat treatment is shown by the solid cyan lines.

It was necessary to demonstrate that the increase in oxygen vacancy content enhanced sensor responsivity. **Figure 4(e)** shows that the ZTO-ZnO film possessed reduced $V_O = 26.2$ %, relative to the ZTO-ZTO film. This TFT was exposed to acetone and IPA vapors overnight and our new findings (see **Figure S10**), clearly show that reduced oxygen vacancy content and poor electrical performance result in a much lower responsivity in both the linear ($V_{ds} = 10$ V) and saturation regimes ($V_{ds} = 40$ V).

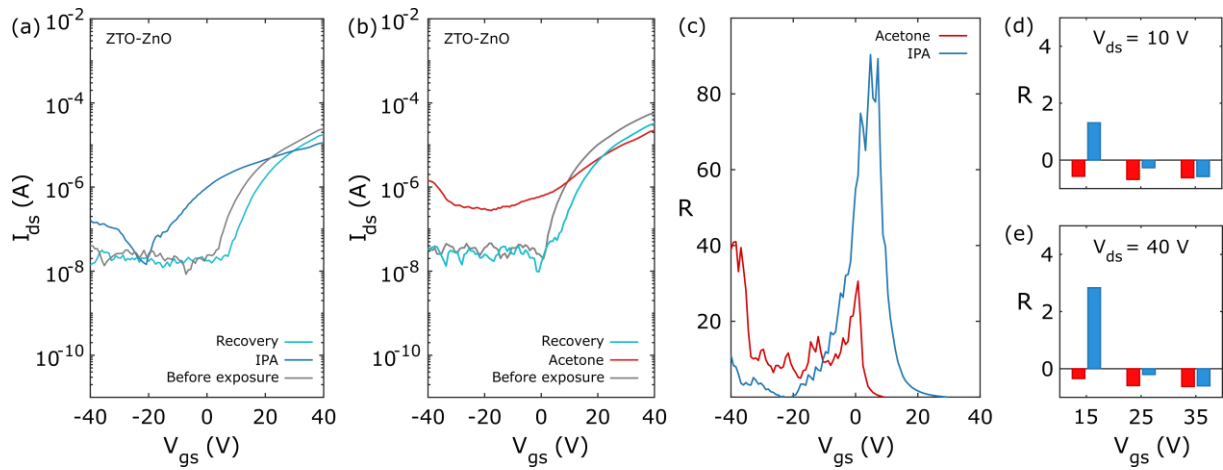


Figure S10. Transfer characteristics in the saturation regime at $V_{ds} = 40$ V, $V_{gs} = -40$ to 40 V and $L = 80$ μm for the ZTO-ZnO TFTs following overnight exposure to (a) IPA and (b) acetone vapors. (c) Calculated responsivity. (d) Transient sensor response at fixed $V_{gs} = 15$ V, 25 V and 35 V in the linear and (e) saturation regimes.

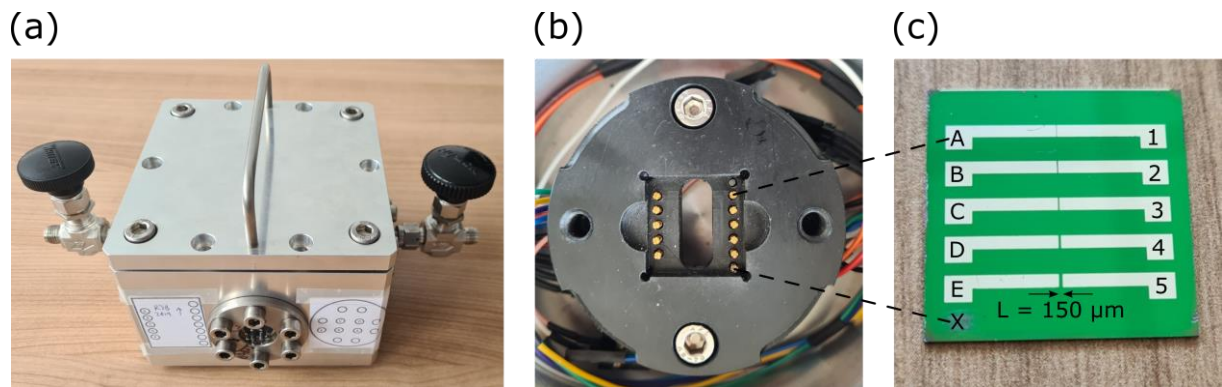


Figure S11. (a) Bespoke testing chamber with (b) device stage illustrations corresponding to (c) source-drain electrodes. The source contact pins were listed from one to five with complementary drain contact pins from A to E. The largest channel length ($L = 150$ μm) corresponded to contacts five and E. The substrate was scratched with a diamond tip pen below pin E to access the gate electrode at pin X and flipped prior to testing.

Tables S6-S8 suggested that V_{th} returned to near-zero following heating in the air as oxygen vacancies were filled by free oxygen due to the dynamic energy of atoms when the temperature was elevated.

Table S6. Electrical properties for $L = 80$ μm , 100 μm & 120 μm obtained before and after the ZTO-ZTO TFTs treated at 500 $^{\circ}\text{C}$ were exposed to IPA in the air.

L (μm)	$I_{on/off}$	V_{th}	μ	μ_{eff}
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			[V]	[cm ² V ⁻¹ s ⁻¹]	[cm ² V ⁻¹ s ⁻¹]
Before exposure		10 ⁵	2.41	3.24	3.01
IPA	80	10 ⁵	-30.9	4.07	4.07
Recovery		10 ⁵	-0.401	3.26	3.08
Before exposure		10 ⁵	3.73	2.32	2.15
IPA	100	10 ⁵	-5.65	3.99	3.80
Recovery		10 ⁵	3.51	2.37	2.15
Before exposure		10 ⁴	2.04	2.35	2.22
IPA	120	10 ⁴	2.23	2.32	2.18
Recovery		10 ⁴	5.62	1.39	1.20

Table S7. Electrical properties for L = 80 μ m, 100 μ m & 120 μ m obtained before and after the ZTO-ZTO TFTs treated at 500 °C were exposed to acetone in the air.

	L (μ m)	I _{on/off}	V _{th} [V]	μ [cm ² V ⁻¹ s ⁻¹]	μ_{eff} [cm ² V ⁻¹ s ⁻¹]
Before exposure		10 ⁵	0.300	3.49	3.31
Acetone	80	10 ³	-34.4	2.19	2.25
Recovery		10 ⁴	0.225	2.79	2.62
Before exposure		10 ⁴	1.68	2.80	2.65
Acetone	100	10 ²	-13.1	2.73	2.68
Recovery		10 ⁴	2.33	2.24	2.06
Before exposure		10 ³	4.48	1.74	1.55
Acetone	120	10 ¹	-3.14	2.11	2.00

Recovery	10^3	4.75	1.40	1.22
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Table S8. Electrical properties for $L = 80 \mu\text{m}$, $100 \mu\text{m}$ & $120 \mu\text{m}$ obtained before and after the ZTO-ZTO TFTs treated at 500°C were exposed to toluene in the air.

	$L (\mu\text{m})$	$I_{\text{on/off}}$	V_{th} [V]	μ [$\text{cm}^2\text{V}^{-1}\text{s}^{-1}$]	μ_{eff} [$\text{cm}^2\text{V}^{-1}\text{s}^{-1}$]
Before exposure	80	10^5	1.05	5.04	4.55
Toluene		10^5	2.18	4.79	4.25
Recovery		10^5	-1.07	4.55	4.13
Before exposure	100	10^5	2.99	3.22	2.84
Toluene		10^4	4.41	2.68	2.27
Recovery		10^4	2.34	3.02	2.68
Before exposure	120	10^4	4.80	1.72	1.44
Toluene		10^4	4.99	1.67	1.89
Recovery		10^4	4.95	1.64	1.36

Table S9. Comparison of the TFT-based gas sensors' performance.

Sensing Material	Gas	Operating Temperature [$^\circ\text{C}$]	R	Concentration [ppm]	Response Time [s]	Recovery Time [s]	Ref
InNdO nanofiber	Acetone	RT ^{a)}	88	4	31	53	[18]
IGZO	NO_2	RT	1330	5	180	180 ^{b)}	[49]
IGZO	Ammonia	RT	-	0.1	120	-	[20]
IGZO	Acetone	RT	0.04	0.1	120	-	[20]
SnO_2	Acetone	RT	1129	-	-	-	[19]

ZTO	Acetone	RT	9326	-	-	-	This work
ZTO							
ZTO	IPA	RT	48664	-	-	-	This work
ZTO							
ZTO	Methanol	RT	1.08 million	-	-	-	This work
ZTO							

^{a)} ((RT = Room-temperature (20 °C); ^{b)} Recovery by UV LED in N₂ purge))